

STEP RECOVERY DIODE CHIP

DESCRIPTION:

The **ASI 5082-0008** is a Silicon Oxide Passivated SRD Chip Designed for hybrid local oscillator Applications.

FEATURES:

- Gold contact metalization
- Passivated Chip

MAXIMUM RATINGS

I	100 mA
V	15 V
P_{DISS}	100 mW @ T _C = 25 °C
T_J	-60 °C to +200 °C
T_{STG}	-65 °C to +200 °C
T_{SOLD}	t ≤ 1.0 MINUTE +310 °C

PACKAGE STYLE CHIP

The diagram illustrates the physical dimensions and components of the chip package. It shows a top view and a side view. The top view is a square with a small circle in the center, labeled 'GOLD PAD DIA'. The side view shows the chip's thickness, labeled '5+/-1'. The distance from the center of the chip to the edge of the pad is labeled 'S+/-2'. The side view also shows the 'GOLD BACK' layer. The label 'SQ' is positioned between the top and side views.

CHIP SIZE CODE X	CHIP SIZE S	PAD SIZE CODE Y	PAD DIA D
1	15	1	1T02
2	20	2	22
3	30		
7	70		

CHIP = 0.020 X 0.020 X 0.011 INCHES
 TOP BOND CONTACT GOLD = 0.0025 INCHES
 BOTTOM CONTACT GOLD (FULL AREA)

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	15			V
C_J	V _R = 10 V f = 1.0 MHz			0.38	pF
R_S	I _F = 20 mA f = 100 MHz		0.8		Ohms
τ	I _F = 10 mA I _R = 6.0 mA		10		μS
t_t	C _L = 100 pc		60		pS